a metal layer provided over said substrate and being in direct contact with a gate electrode of said thin film transistor and being connected with one of source and drain regions of said thin film transistor.

57. The device of claim 56 wherein said electro-optical device is a liquid crystal display.

Cont. B1

58. An electro-optical device comprising:

a substrate;

a thin film transistor provided over said substrate in a peripheral circuit of said electro-optical device; and

a metal layer provided over said substrate and being in direct contact with a gate electrode of said thin film transistor and being connected with one of source and drain regions of said thin film transistor.

59. The device of claim 58 wherein said electro-optical device is a liquid crystal display.

60. An integrated circuit comprising:

a substrate;

a thin film transistor provided over said substrate; and

a metal layer provided over said substrate and being in direct contact with a gate electrode of said thin film transistor and being connected with one of source and drain regions of said thin film transistor.

60. An electro optical device comprising:

a substrate;

a source region and a drain region provided over said substrate;

a channel region provided over said substrate between said source region and said drain region;

a gate electrode provided adjacent to said channel region with a gate insulating film therebetween;

a gate interconnect provided in a same layer as said gate electrode;

a metal layer comprising titanium provided over said substrate and being in direct contact with said gate interconnect and being connected with one of said source region and said drain region;

an interlayer dielectric provided over said gate electrode and said metal layer;

a contact hole provided over said metal layer in said interlayer dielectric; and

a top layer interconnected comprising aluminum provided over said interlayer dielectric and connected with said metal layer through said contact hole.

62. The device of claim 61 wherein said contact hole is located outside said source region and said drain region.

Cont. B1

63. The device of claim 56 wherein said metal layer is connected with said gate electrode through no contact hole.

64. The device of claim 56 wherein said thin film transistor is an n-channel thin film transistor.

65. The device of claim 56 wherein said thin film transistor is a p-channel thin film transistor.

66. The device of claim 58 wherein said thin film transistor is an n-channel thin film transistor.

67. The device of claim 58 wherein said thin film transistor is an n-channel thin film transistor.

68. The device of claim 60 wherein said thin film transistor is an n-channel thin film transistor.

69. The device of claim 60 wherein said thin film transistor is a p-channel thin film transistor.

Cont'd B1

70. The device of claim 58 wherein said metal layer is connected with said gate electrode through no contact hole.

71. The device of claim 60 wherein said metal layer is connected with said gate electrode through no contact hole.

72. The device of claim 61 wherein said metal layer is connected with said gate interconnect through no contact hole.

REMARKS

Entry of the additional claims noted above is requested. Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: 3/6/00

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